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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I ² C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	DMA, Motor Control PWM, PDR, POR, PVD, PWM, Temp Sensor, WDT
Number of I/O	51
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	10K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f103r6t6a

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2 Description

The STM32F103x4 and STM32F103x6 performance line family incorporates the high-performance ARM® Cortex™-M3 32-bit RISC core operating at a 72 MHz frequency, high-speed embedded memories (Flash memory up to 32 Kbytes and SRAM up to 6 Kbytes), and an extensive range of enhanced I/Os and peripherals connected to two APB buses. All devices offer two 12-bit ADCs, three general purpose 16-bit timers plus one PWM timer, as well as standard and advanced communication interfaces: up to two I²Cs and SPIs, three USARTs, an USB and a CAN.

The STM32F103xx low-density performance line family operates from a 2.0 to 3.6 V power supply. It is available in both the –40 to +85 °C temperature range and the –40 to +105 °C extended temperature range. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F103xx low-density performance line family includes devices in four different package types: from 36 pins to 64 pins. Depending on the device chosen, different sets of peripherals are included, the description below gives an overview of the complete range of peripherals proposed in this family.

These features make the STM32F103xx low-density performance line microcontroller family suitable for a wide range of applications such as motor drives, application control, medical and handheld equipment, PC and gaming peripherals, GPS platforms, industrial applications, PLCs, inverters, printers, scanners, alarm systems, video intercoms, and HVACs.

This hardware block provides flexible interrupt management features with minimal interrupt latency.

2.3.6 External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 19 edge detector lines used to generate interrupt/event requests. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 51 GPIOs can be connected to the 16 external interrupt lines.

2.3.7 Clocks and startup

System clock selection is performed on startup, however the internal RC 8 MHz oscillator is selected as default CPU clock on reset. An external 4-16 MHz clock can be selected, in which case it is monitored for failure. If failure is detected, the system automatically switches back to the internal RC oscillator. A software interrupt is generated if enabled. Similarly, full interrupt management of the PLL clock entry is available when necessary (for example on failure of an indirectly used external crystal, resonator or oscillator).

Several prescalers allow the configuration of the AHB frequency, the high-speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the high-speed APB domains is 72 MHz. The maximum allowed frequency of the low-speed APB domain is 36 MHz. See [Figure 2](#) for details on the clock tree.

2.3.8 Boot modes

At startup, boot pins are used to select one of three boot options:

- Boot from User Flash
- Boot from System Memory
- Boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART1. For further details please refer to AN2606.

2.3.9 Power supply schemes

- $V_{DD} = 2.0$ to 3.6 V: external power supply for I/Os and the internal regulator. Provided externally through V_{DD} pins.
- V_{SSA} , $V_{DDA} = 2.0$ to 3.6 V: external analog power supplies for ADC, reset blocks, RCs and PLL (minimum voltage to be applied to V_{DDA} is 2.4 V when the ADC is used). V_{DDA} and V_{SSA} must be connected to V_{DD} and V_{SS} , respectively.
- $V_{BAT} = 1.8$ to 3.6 V: power supply for RTC, external clock 32 kHz oscillator and backup registers (through power switch) when V_{DD} is not present.

For more details on how to connect power pins, refer to [Figure 11: Power supply scheme](#).

2.3.10 Power supply supervisor

The device has an integrated power-on reset (POR)/power-down reset (PDR) circuitry. It is always active, and ensures proper operation starting from/down to 2 V. The device remains

Table 5. Low-density STM32F103xx pin definitions

Pins				Pin name	Type ⁽¹⁾	I/O Level ⁽²⁾	Main function ⁽³⁾ (after reset)	Alternate functions ⁽⁴⁾	
LQFP48/ UFQFPN48	LQFP64	TFBGA64	VFQFPN36					Default	Remap
1	1	B2	-	V _{BAT}	S	-	V _{BAT}	-	-
2	2	A2	-	PC13-TAMPER-RTC ⁽⁵⁾	I/O	-	PC13 ⁽⁶⁾	TAMPER-RTC	-
3	3	A1	-	PC14-OSC32_IN ⁽⁵⁾	I/O	-	PC14 ⁽⁶⁾	OSC32_IN	-
4	4	B1	-	PC15-OSC32_OUT ⁽⁵⁾	I/O	-	PC15 ⁽⁶⁾	OSC32_OUT	-
5	5	C1	2	OSC_IN	I	-	OSC_IN	-	PD0 ⁽⁷⁾
6	6	D1	3	OSC_OUT	O	-	OSC_OUT	-	PD1 ⁽⁷⁾
7	7	E1	4	NRST	I/O	-	NRST	-	-
-	8	E3	-	PC0	I/O	-	PC0	ADC12_IN10	-
-	9	E2	-	PC1	I/O	-	PC1	ADC12_IN11	-
-	10	F2	-	PC2	I/O	-	PC2	ADC12_IN12	-
-	11	-	-	PC3	I/O	-	PC3	ADC12_IN13	-
-	-	G1	-	V _{REF+} ⁽⁸⁾	S	-	V _{REF+}	-	-
8	12	F1	5	V _{SSA}	S	-	V _{SSA}	-	-
9	13	H1	6	V _{DDA}	S	-	V _{DDA}	-	-
10	14	G2	7	PA0-WKUP	I/O	-	PA0	WKUP/USART2_CTS/ ADC12_IN0/ TIM2_CH1_ETR ⁽⁹⁾	-
11	15	H2	8	PA1	I/O	-	PA1	USART2_RTS/ ADC12_IN1/TIM2_CH2 ⁽⁹⁾	-
12	16	F3	9	PA2	I/O	-	PA2	USART2_TX/ ADC12_IN2/TIM2_CH3 ⁽⁹⁾	-
13	17	G3	10	PA3	I/O	-	PA3	USART2_RX/ ADC12_IN3/TIM2_CH4 ⁽⁹⁾	-
-	18	C2	-	V _{SS_4}	S	-	V _{SS_4}	-	-
-	19	D2	-	V _{DD_4}	S	-	V _{DD_4}	-	-
14	20	H3	11	PA4	I/O	-	PA4	SPI1_NSS ⁽⁹⁾ / USART2_CK/ADC12_IN4	-
15	21	F4	12	PA5	I/O	-	PA5	SPI1_SCK ⁽⁹⁾ /ADC12_IN5	-
16	22	G4	13	PA6	I/O	-	PA6	SPI1_MISO ⁽⁹⁾ / ADC12_IN6/TIM3_CH1 ⁽⁹⁾	TIM1_BKIN
17	23	H4	14	PA7	I/O	-	PA7	SPI1_MOSI ⁽⁹⁾ / ADC12_IN7/TIM3_CH2 ⁽⁹⁾	TIM1_CH1N
-	24	H5	-	PC4	I/O	-	PC4	ADC12_IN14	-
-	25	H6	-	PC5	I/O	-	PC5	ADC12_IN15	-

5 Electrical characteristics

5.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS} .

5.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at $T_A = 25\text{ °C}$ and $T_A = T_{Amax}$ (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation ($\text{mean} \pm 3\sigma$).

5.1.2 Typical values

Unless otherwise specified, typical data are based on $T_A = 25\text{ °C}$, $V_{DD} = 3.3\text{ V}$ (for the $2\text{ V} \leq V_{DD} \leq 3.6\text{ V}$ voltage range). They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated ($\text{mean} \pm 2\sigma$).

5.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

5.1.4 Loading capacitor

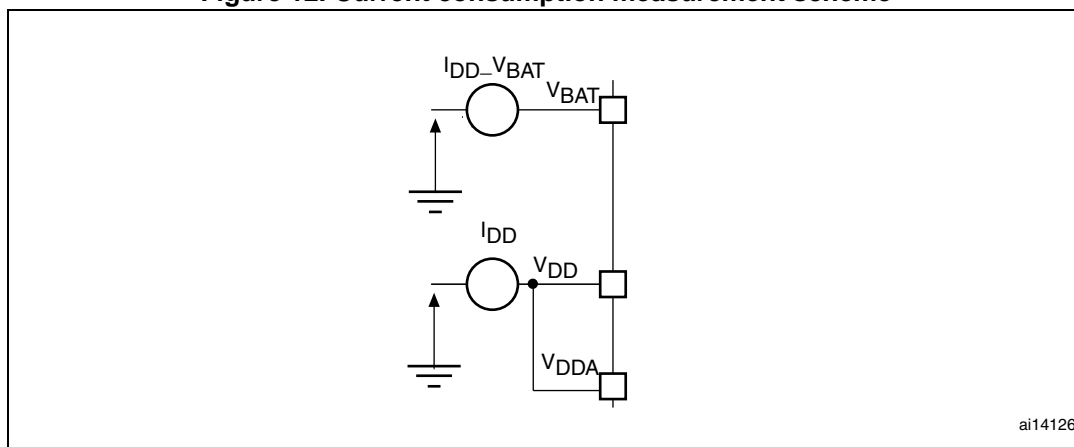
The loading conditions used for pin parameter measurement are shown in [Figure 9](#).

5.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in [Figure 10](#).

5.1.7 Current consumption measurement

Figure 12. Current consumption measurement scheme



5.2 Absolute maximum ratings

Stresses above the absolute maximum ratings listed in [Table 6: Voltage characteristics](#), [Table 7: Current characteristics](#), and [Table 8: Thermal characteristics](#) may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Table 6. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD} - V_{SS}$	External main supply voltage (including V_{DDA} and V_{DD}) ⁽¹⁾	-0.3	4.0	V
$V_{IN}^{(2)}$	Input voltage on five volt tolerant pin	$V_{SS} - 0.3$	$V_{DD} + 4.0$	
	Input voltage on any other pin	$V_{SS} - 0.3$	4.0	
$ \Delta V_{DDx} $	Variations between different V_{DD} power pins	-	50	mV
$ V_{SSx} - V_{SS} $	Variations between all the different ground pins	-	50	
$V_{ESD(HBM)}$	Electrostatic discharge voltage (human body model)	see Section 5.3.11: Absolute maximum ratings (electrical sensitivity)		-

1. All main power (V_{DD} , V_{DDA}) and ground (V_{SS} , V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. V_{IN} maximum must always be respected. Refer to [Table 7: Current characteristics](#) for the maximum allowed injected current values.

Figure 19. High-speed external clock source AC timing diagram

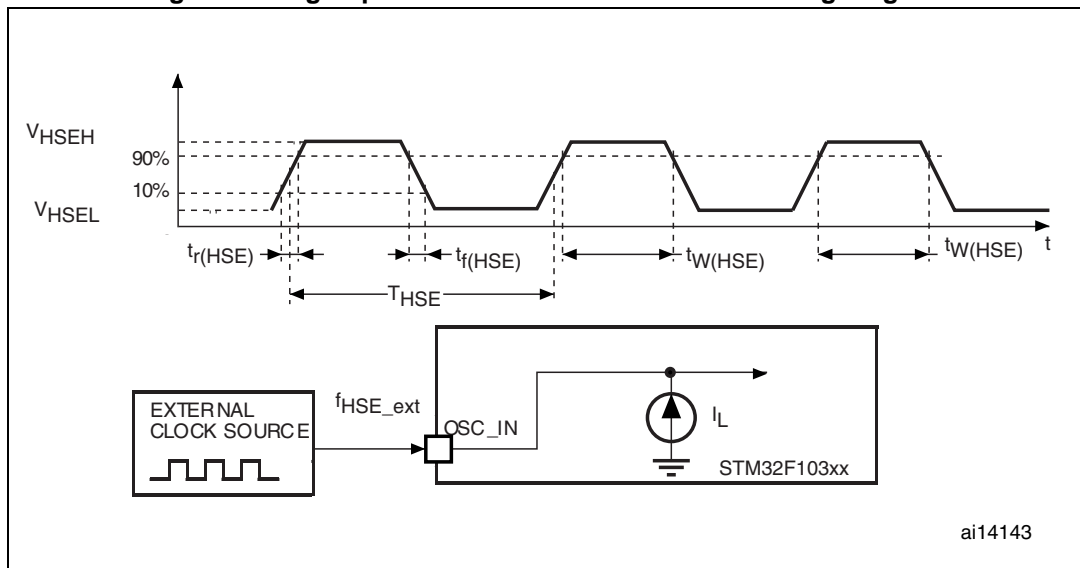
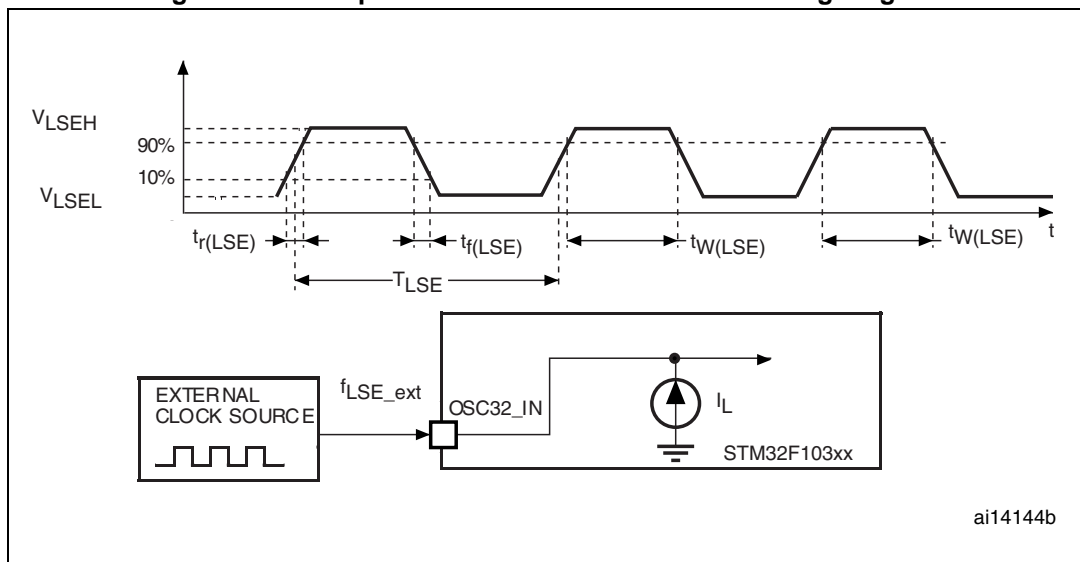


Figure 20. Low-speed external clock source AC timing diagram



High-speed external clock generated from a crystal/ceramic resonator

The high-speed external (HSE) clock can be supplied with a 4 to 16 MHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on characterization results obtained with typical external components specified in [Table 22](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 28. Flash memory characteristics (continued)

Symbol	Parameter	Conditions	Min ⁽¹⁾	Typ	Max ⁽¹⁾	Unit
I _{DD}	Supply current	Read mode f _{HCLK} = 72 MHz with 2 wait states, V _{DD} = 3.3 V	-	-	20	mA
		Write / Erase modes f _{HCLK} = 72 MHz, V _{DD} = 3.3 V	-	-	5	mA
		Power-down mode / Halt, V _{DD} = 3.0 to 3.6 V	-	-	50	μA
V _{prog}	Programming voltage	-	2	-	3.6	V

1. Guaranteed by design, not tested in production.

Table 29. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value			Unit
			Min ⁽¹⁾	Typ	Max	
N _{END}	Endurance	T _A = -40 to +85 °C (6 suffix versions) T _A = -40 to +105 °C (7 suffix versions)	10	-	-	kcycles
t _{RET}	Data retention	1 kcycle ⁽²⁾ at T _A = 85 °C	30	-	-	Years
		1 kcycle ⁽²⁾ at T _A = 105 °C	10	-	-	
		10 kcycles ⁽²⁾ at T _A = 55 °C	20	-	-	

1. Based on characterization, not tested in production.

2. Cycling performed over the whole temperature range.

5.3.10 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports), the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB:** A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in [Table 30](#). They are based on the EMS levels and classes defined in application note AN1709.

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in [Figure 27](#) and [Table 37](#), respectively.

Unless otherwise specified, the parameters given in [Table 37](#) are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in [Table 9](#).

Table 37. I/O AC characteristics⁽¹⁾

MODEx[1:0]] bit value ⁽¹⁾	Symbol	Parameter	Conditions	Min	Max	Unit
10	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽²⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 3.6 \text{ V}$	-	2	MHz
	$t_{f(\text{IO})\text{out}}$	Output high to low level fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 3.6 \text{ V}$	-	125 ⁽³⁾	ns
	$t_{r(\text{IO})\text{out}}$	Output low to high level rise time		-	125 ⁽³⁾	
01	$f_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽²⁾	$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 3.6 \text{ V}$	-	10	MHz
	$t_{f(\text{IO})\text{out}}$	Output high to low level fall time	$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 3.6 \text{ V}$	-	25 ⁽³⁾	ns
	$t_{r(\text{IO})\text{out}}$	Output low to high level rise time		-	25 ⁽³⁾	
11	$F_{\max(\text{IO})\text{out}}$	Maximum frequency ⁽²⁾	$C_L = 30 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	50	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	30	MHz
			$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 2.7 \text{ V}$	-	20	MHz
	$t_{f(\text{IO})\text{out}}$	Output high to low level fall time	$C_L = 30 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	5 ⁽³⁾	ns
			$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	8 ⁽³⁾	
			$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 2.7 \text{ V}$	-	12 ⁽³⁾	
	$t_{r(\text{IO})\text{out}}$	Output low to high level rise time	$C_L = 30 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	5 ⁽³⁾	
			$C_L = 50 \text{ pF}$, $V_{DD} = 2.7 \text{ V to } 3.6 \text{ V}$	-	8 ⁽³⁾	
			$C_L = 50 \text{ pF}$, $V_{DD} = 2 \text{ V to } 2.7 \text{ V}$	-	12 ⁽³⁾	
-	$t_{\text{EXTI}pw}$	Pulse width of external signals detected by the EXTI controller	-	10	-	ns

1. The I/O speed is configured using the MODEx[1:0] bits. Refer to the STM32F10xxx reference manual for a description of GPIO Port configuration register.
2. The maximum frequency is defined in [Figure 27](#).
3. Guaranteed by design, not tested in production.

5.3.16 Communications interfaces

I²C interface characteristics

The STM32F103xx performance line I²C interface meets the requirements of the standard I²C communication protocol with the following restrictions: the I/O pins SDA and SCL are mapped to are not “true” open-drain. When configured as open-drain, the PMOS connected between the I/O pin and V_{DD} is disabled, but is still present.

The I²C characteristics are described in [Table 40](#). Refer also to [Section 5.3.12: I/O current injection characteristics](#) for more details on the input/output alternate function characteristics (SDA and SCL).

Table 40. I²C characteristics

Symbol	Parameter	Standard mode I ² C ⁽¹⁾⁽²⁾		Fast mode I ² C ⁽¹⁾⁽²⁾		Unit
		Min	Max	Min	Max	
t _w (SCLL)	SCL clock low time	4.7	-	1.3	-	μs
t _w (SCLH)	SCL clock high time	4.0	-	0.6	-	
t _{su} (SDA)	SDA setup time	250	-	100	-	ns
t _h (SDA)	SDA data hold time	-	3450 ⁽³⁾	-	900 ⁽³⁾	
t _r (SDA) t _r (SCL)	SDA and SCL rise time	-	1000	-	300	
t _f (SDA) t _f (SCL)	SDA and SCL fall time	-	300	-	300	
t _h (STA)	Start condition hold time	4.0	-	0.6	-	μs
t _{su} (STA)	Repeated Start condition setup time	4.7	-	0.6	-	
t _{su} (STO)	Stop condition setup time	4.0	-	0.6	-	μs
t _w (STO:STA)	Stop to Start condition time (bus free)	4.7	-	1.3	-	μs
C _b	Capacitive load for each bus line	-	400	-	400	pF

1. Guaranteed by design, not tested in production.
2. f_{PCLK1} must be at least 2 MHz to achieve standard mode I²C frequencies. It must be at least 4 MHz to achieve fast mode I²C frequencies. It must be a multiple of 10 MHz to reach the 400 kHz maximum I²C fast mode clock.
3. The maximum Data hold time has only to be met if the interface does not stretch the low period of SCL signal.

Table 49. ADC accuracy^{(1) (2) (3)}

Symbol	Parameter	Test conditions	Typ	Max ⁽⁴⁾	Unit
ET	Total unadjusted error	$f_{PCLK2} = 56 \text{ MHz}$, $f_{ADC} = 14 \text{ MHz}$, $R_{AIN} < 10 \text{ k}\Omega$, $V_{DDA} = 2.4 \text{ V to } 3.6 \text{ V}$ Measurements made after ADC calibration	± 2	± 5	LSB
EO	Offset error		± 1.5	± 2.5	
EG	Gain error		± 1.5	± 3	
ED	Differential linearity error		± 1	± 2	
EL	Integral linearity error		± 1.5	± 3	

1. ADC DC accuracy values are measured after internal calibration.
2. Better performance could be achieved in restricted V_{DD} , frequency and temperature ranges.
3. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in [Section 5.3.12](#) does not affect the ADC accuracy.
4. Based on characterization, not tested in production.

Figure 34. ADC accuracy characteristics

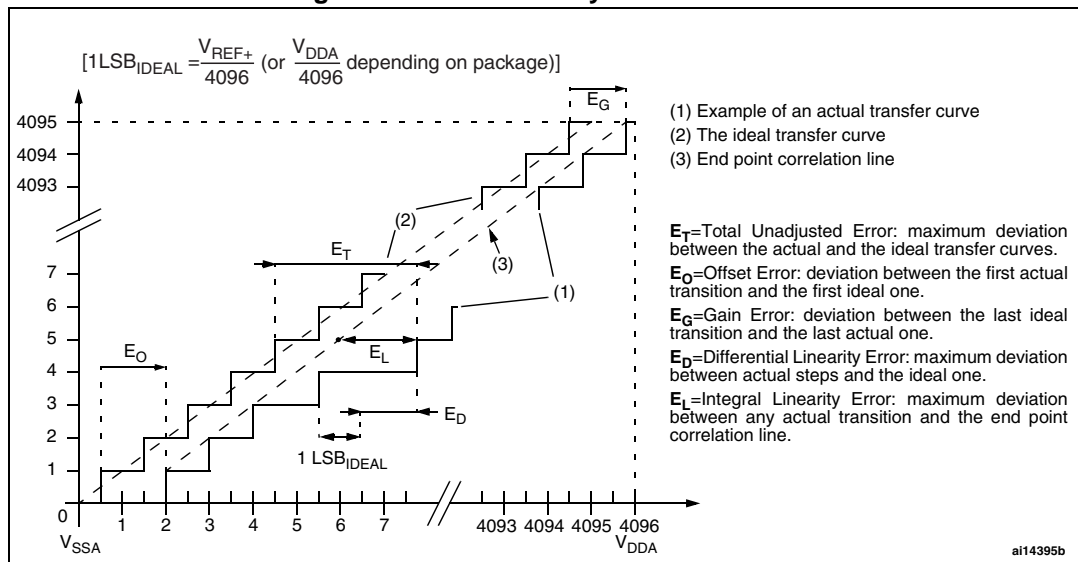
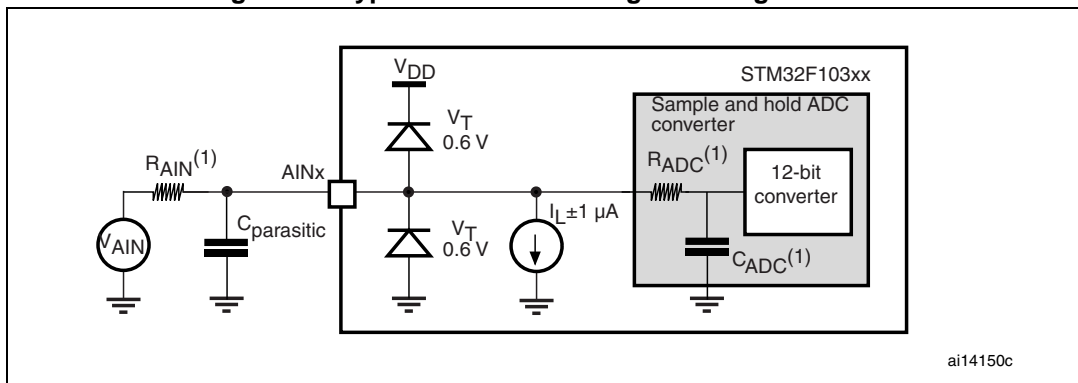


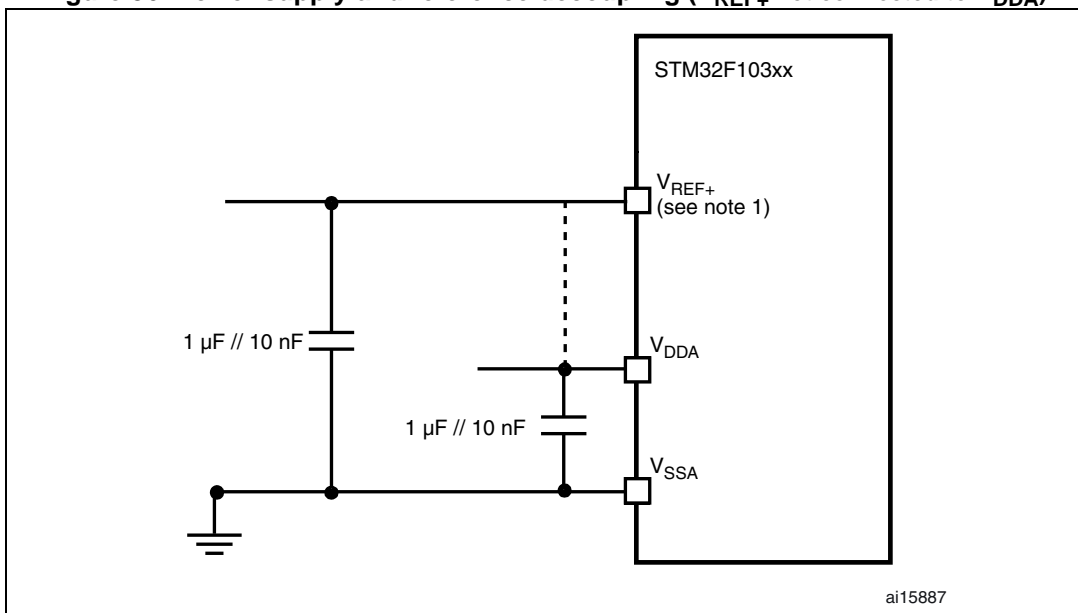
Figure 35. Typical connection diagram using the ADC



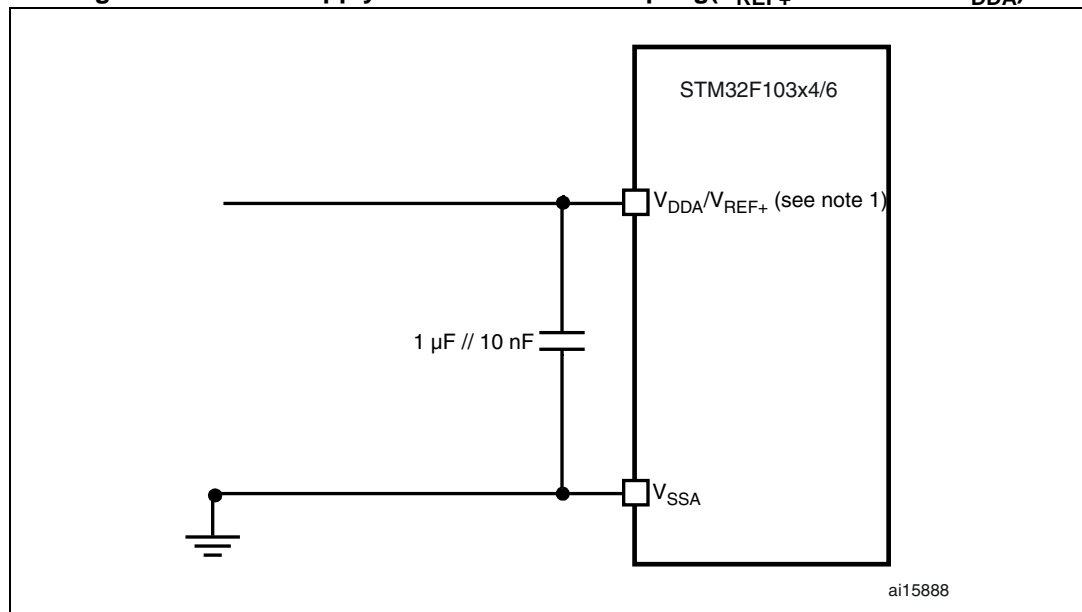
1. Refer to [Table 46](#) for the values of R_{AIN} , R_{ADC} and C_{ADC} .
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in [Figure 36](#) or [Figure 37](#), depending on whether V_{REF+} is connected to V_{DDA} or not. The 10 nF capacitors should be ceramic (good quality). They should be placed them as close as possible to the chip.

Figure 36. Power supply and reference decoupling (V_{REF+} not connected to V_{DDA})

1. The V_{REF+} input is available only on the TFBGA64 package.

Figure 37. Power supply and reference decoupling (V_{REF+} connected to V_{DDA})

1. The V_{REF+} input is available only on the TFBGA64 package.

5.3.19 Temperature sensor characteristics

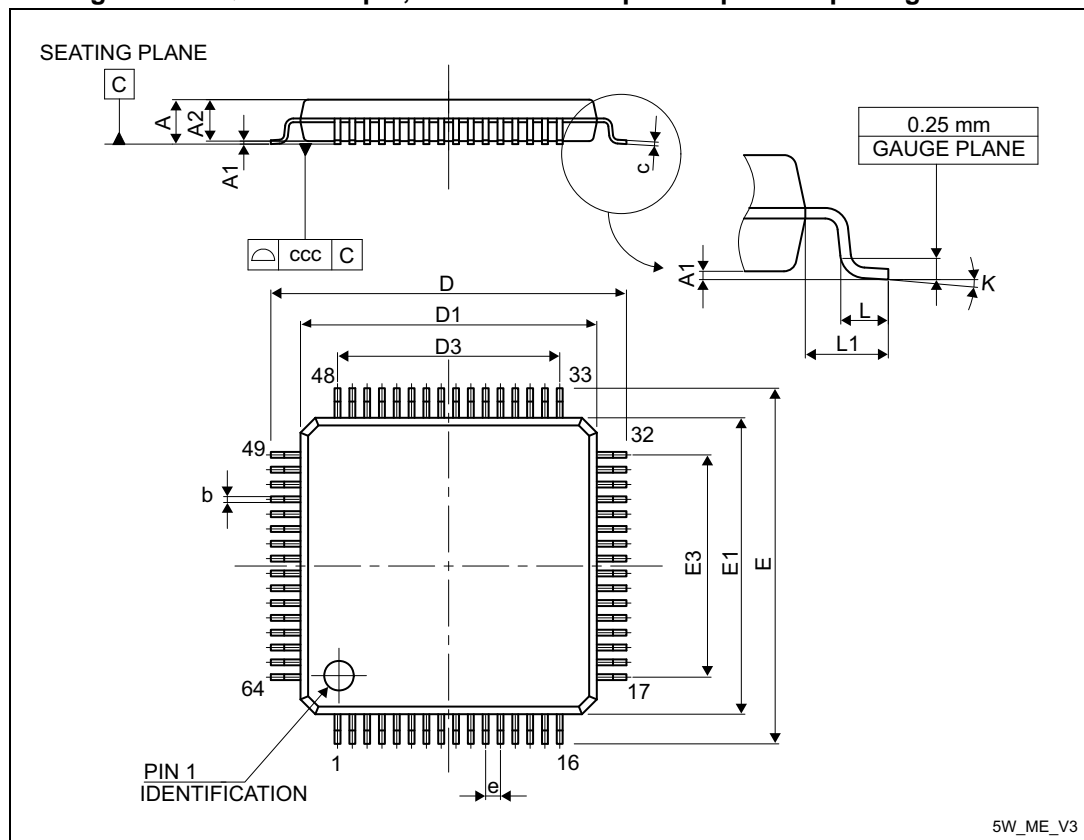
Table 50. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{SENSE} linearity with temperature	-	± 1	± 2	$^{\circ}\text{C}$
Avg_Slope ⁽¹⁾	Average slope	4.0	4.3	4.6	mV/ $^{\circ}\text{C}$
$V_{25}^{(1)}$	Voltage at 25 $^{\circ}\text{C}$	1.34	1.43	1.52	V
$t_{START}^{(2)}$	Startup time	4	-	10	μs
$T_{S_temp}^{(3)(2)}$	ADC sampling time when reading the temperature	-	-	17.1	μs

1. Based on characterization, not tested in production.
2. Guaranteed by design, not tested in production.
3. Shortest sampling time can be determined in the application by multiple iterations.

6.3 LQFP64 package information

Figure 44. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package outline



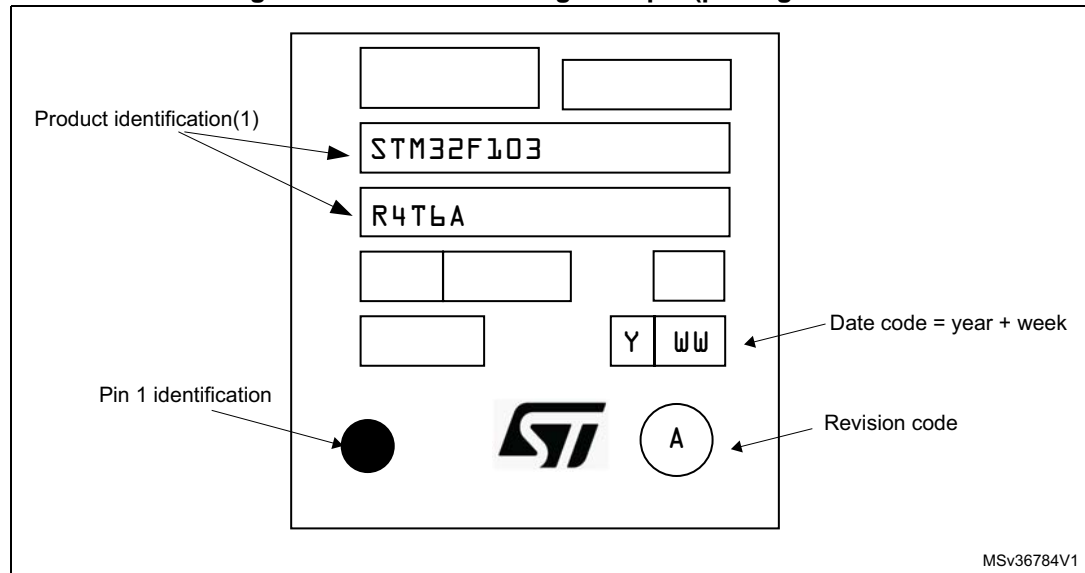
1. Drawing is not to scale.

Table 53. LQFP64 - 64-pin, 10 x 10 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches ⁽¹⁾		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

Device Marking for LQFP64

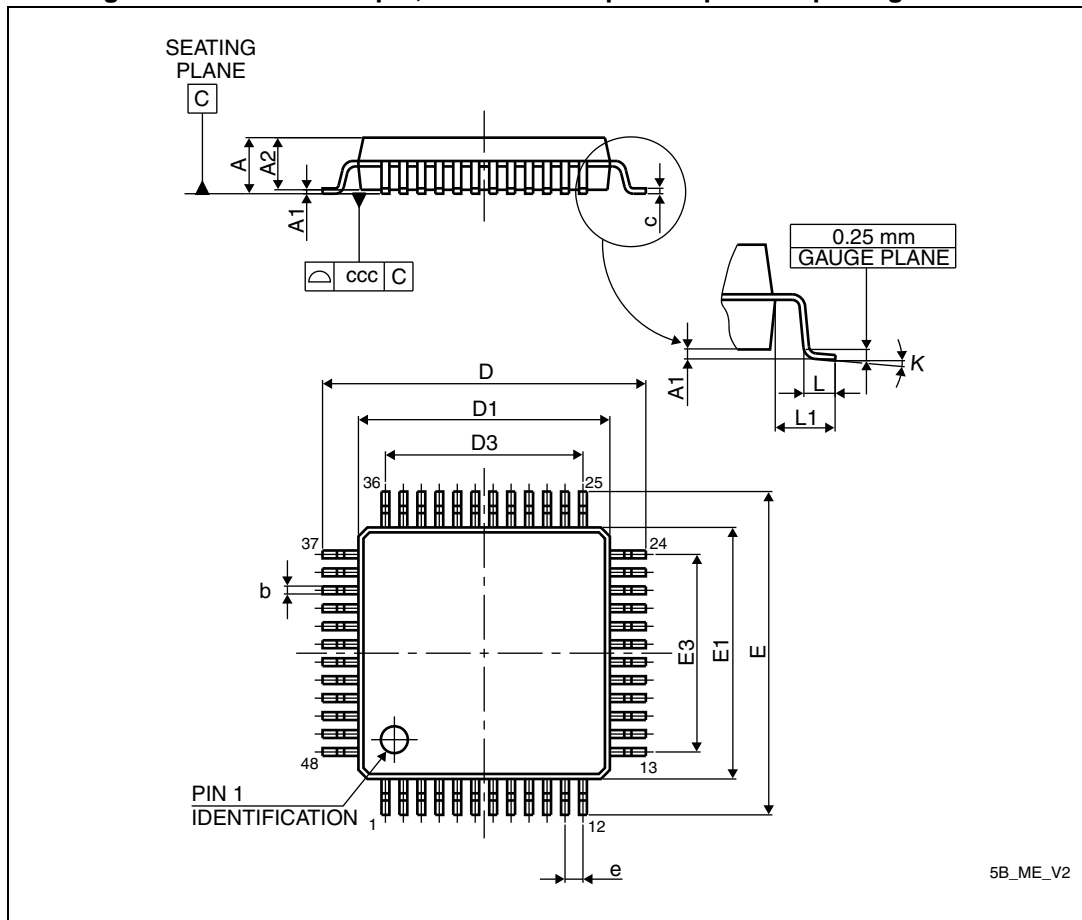
The following figure gives an example of topside marking orientation versus ball 1 identifier location.

Figure 46. LQFP64 marking example (package view)

1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

6.5 LQFP48 package information

Figure 50. LQFP48 - 48-pin, 7 x 7 mm low-profile quad flat package outline



1. Drawing is not to scale.

Using the values obtained in [Table 57](#) T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

$$T_{Jmax} = 115\text{ °C} + (45\text{ °C/W} \times 134\text{ mW}) = 115\text{ °C} + 6.03\text{ °C} = 121.03\text{ °C}$$

This is within the range of the suffix 7 version parts ($-40 < T_J < 125\text{ °C}$).

In this case, parts must be ordered at least with the temperature range suffix 7 (see [Table 58: Ordering information scheme](#)).

Figure 53. LQFP64 P_D max vs. T_A

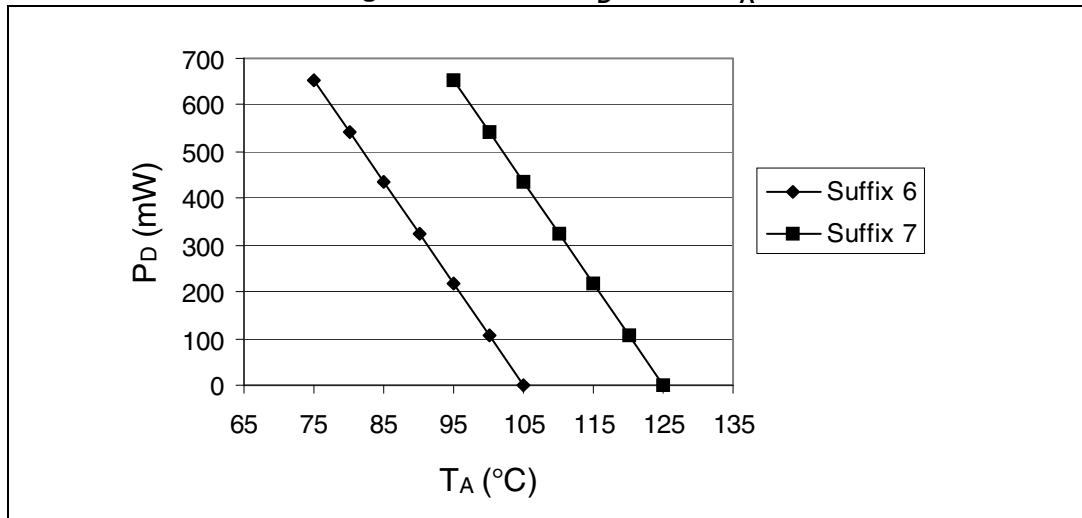


Table 59. Document revision history (continued)

Date	Revision	Changes
14-May-2013	6	<p>Replaced VQFN48 package with UQFN48 in cover page packages, Table 2: STM32F103xx low-density device features and peripheral counts, Figure 6: STM32F103xx performance line UFQFPN48 pinout, Table 5: Low-density STM32F103xx pin definitions, Table 58: Ordering information scheme, updated Table 9: General operating conditions, updated Table 57: Package thermal characteristics, added Figure 41: UFQFPN48 7 x 7 mm, 0.5 mm pitch, package outline and Table 52: UFQFPN48 7 x 7 mm, 0.5 mm pitch, package mechanical data</p> <p>Added footnote for TFBGA ADC channels in Table 2: STM32F103xx low-density device features and peripheral counts</p> <p>Updated 'All GPIOs are high current...' in Section 2.3.21: GPIOs (general-purpose inputs/outputs)</p> <p>Updated Table 5: Low-density STM32F103xx pin definitions</p> <p>Corrected Sigma letter in Section 5.1.1: Minimum and maximum values</p> <p>Updated Table 7: Current characteristics</p> <p>Added 'V_{IN}' in Table 9: General operating conditions</p> <p>Removed the first sentence in Section 5.3.16: Communications interfaces</p> <p>Updated first sentence in Output driving current</p> <p>Added note 5. in Table 24: HSI oscillator characteristics</p> <p>Updated 'V_{IL}' and 'V_{IH}' in Table 35: I/O static characteristics</p> <p>Added notes to Figure 23: Standard I/O input characteristics - CMOS port, Figure 24: Standard I/O input characteristics - TTL port, Figure 25: 5 V tolerant I/O input characteristics - CMOS port and Figure 26: 5 V tolerant I/O input characteristics - TTL port</p> <p>Updated Figure 29: I²C bus AC waveforms and measurement circuit</p> <p>Updated note 2. and 3., removed note "the device must internally..." in Table 40: I²C characteristics</p> <p>Updated title of Table 41: SCL frequency (f_{PCLK1} = 36 MHz., V_{DD_I2C} = 3.3 V)</p> <p>Updated note 2. in Table 49: ADC accuracy</p> <p>Updated Figure 47: TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package outline and Table 54: TFBGA64 - 8 x 8 active ball array, 5 x 5 mm, 0.5 mm pitch, package mechanical data</p>
01-June-2015	7	<p>Added:</p> <ul style="list-style-type: none"> Package's marking pictures(Figure 40, Figure 43, Figure 46, Figure 49, Figure 52) <p>Updated:</p> <ul style="list-style-type: none"> Table 40: I²C characteristics Section 6: Package information